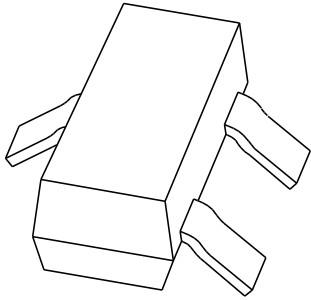


# DATA SHEET



## **BAS678** High-speed diode

Product specification  
Supersedes data of April 1996  
File under Discrete Semiconductors, SC01

1996 Sep 10

# High-speed diode

# BAS678

### FEATURES

- Small plastic SMD package
- High switching speed: max. 6 ns
- Continuous reverse voltage: max. 80 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 600 mA.

### APPLICATIONS

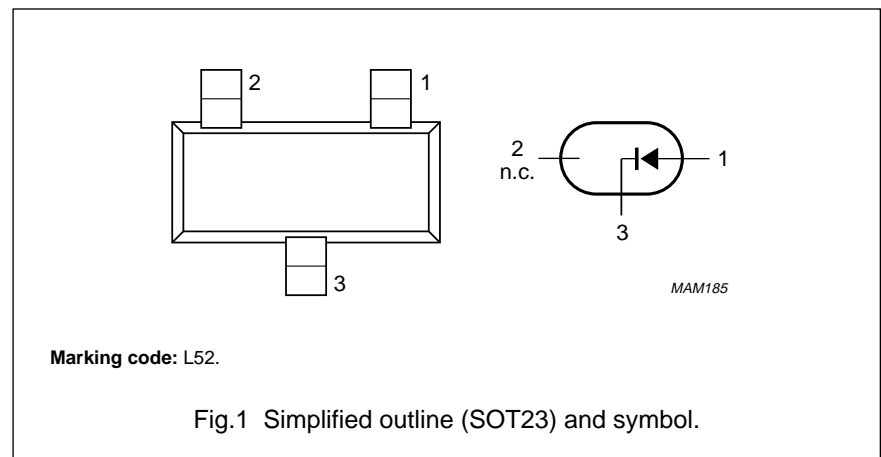
- High-speed switching in hybrid thick and thin-film circuits.

### DESCRIPTION

The BAS678 is a high-speed switching diode fabricated in planar technology, and encapsulated in the small rectangular plastic SMD SOT23 package.

### PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		–	100	V
$V_R$	continuous reverse voltage		–	80	V
$I_F$	continuous forward current	see Fig.2; note 1	–	250	mA
$I_{FRM}$	repetitive peak forward current		–	600	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 100\ \mu\text{s}$ $t = 10\ \text{ms}$	–	9 3 1.7	A A A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; note 1	–	250	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C

### Note

1. Device mounted on an FR4 printed-circuit board.

## High-speed diode

## BAS678

**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ }^\circ\text{C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_F$	forward voltage	see 3; $I_F = 200\text{ mA}$ ; d.c.; note 1	–	1.0	V
$I_R$	reverse current	see Fig.5 $V_R = 10\text{ V}$ $V_R = 75\text{ V}$ $V_R = 75\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$	– – –	15 100 50	nA nA $\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}$ ; $V_R = 0$ ; see Fig.6	–	2	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 400\text{ mA}$ to $I_R = 400\text{ mA}$ ; $R_L = 100\ \Omega$ ; measured at $I_R = 40\text{ mA}$ ; see Fig.7	–	6	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 10\text{ mA}$ ; $t_r = 20\text{ ns}$ ; see Fig.8	–	2	V

**Note**

- $T_{amb} = 25\text{ }^\circ\text{C}$ ; device has reached the thermal equilibrium when mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		330	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

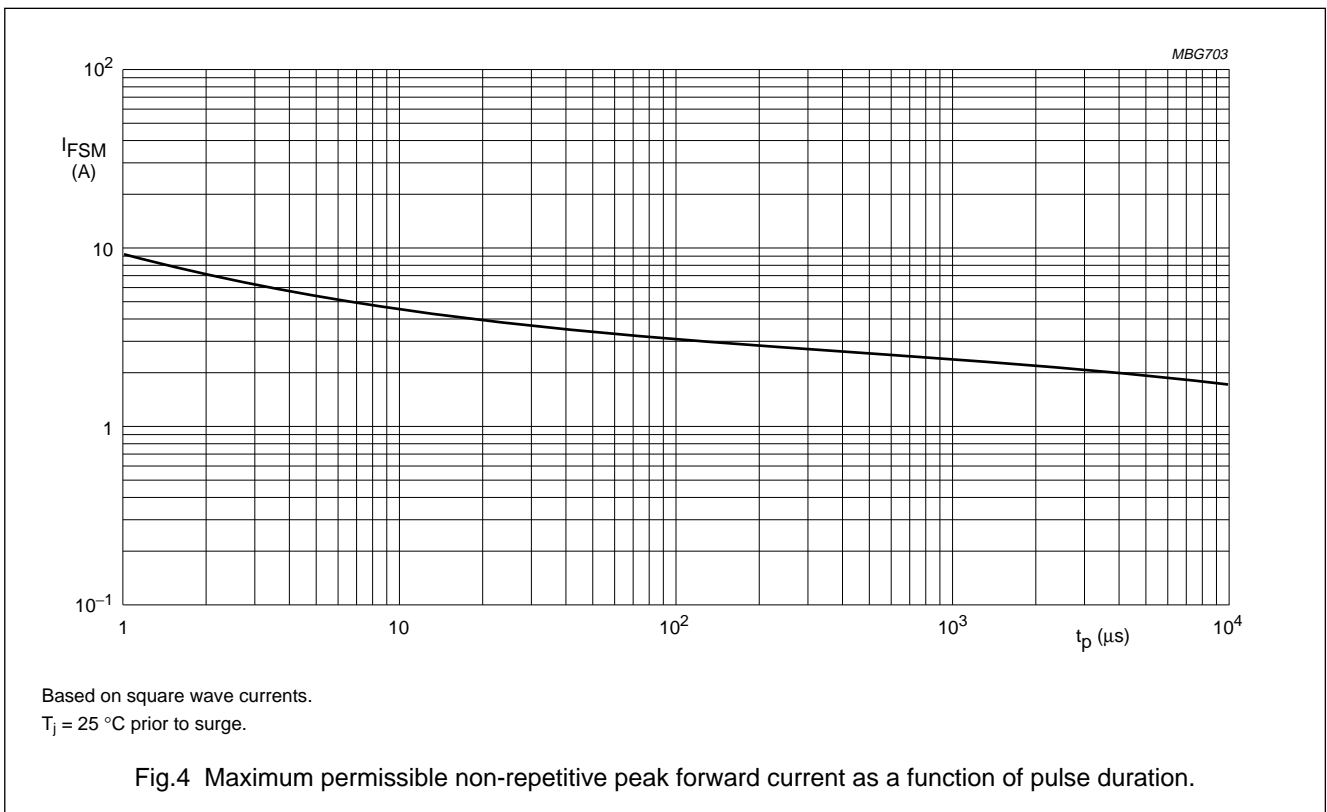
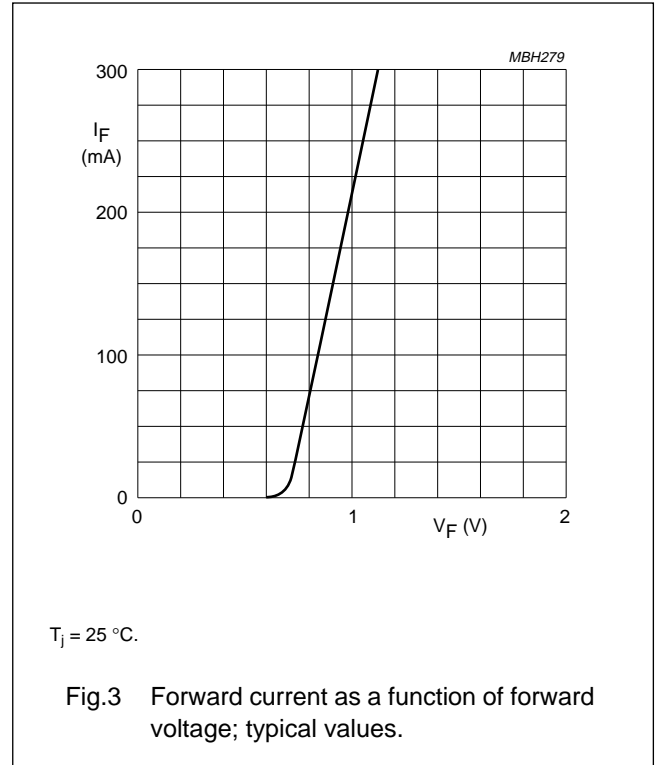
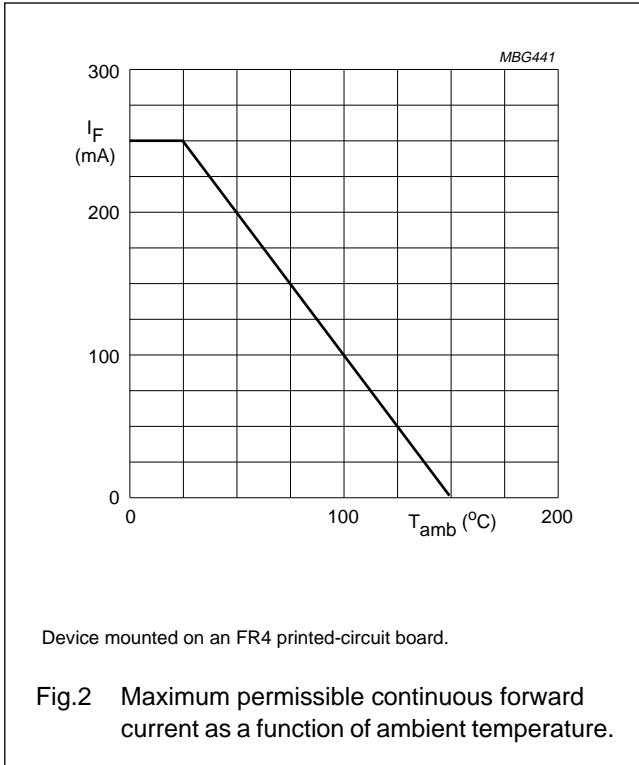
**Note**

- Device mounted on an FR4 printed-circuit board.

High-speed diode

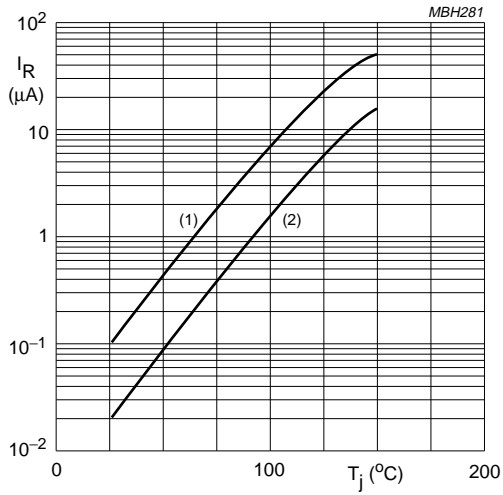
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GRAPHICAL DATA



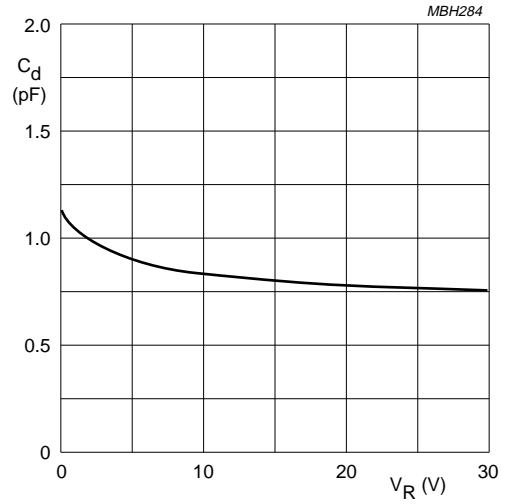
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- (1)  $V_R = 75$  V; maximum values.
- (2)  $V_R = 75$  V; typical values.

Fig.5 Reverse current as a function of junction temperature.



$f = 1$  MHz;  $T_j = 25$  °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

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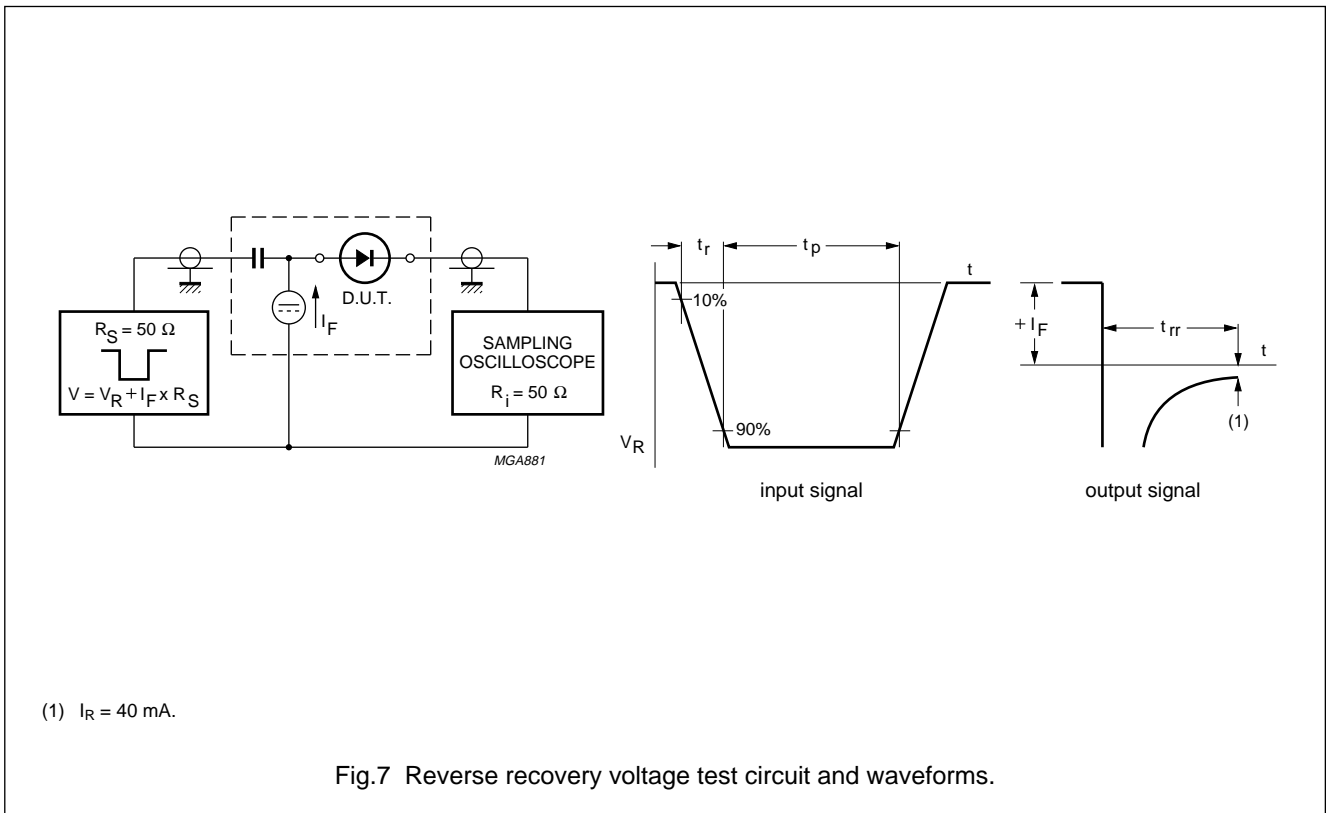


Fig.7 Reverse recovery voltage test circuit and waveforms.

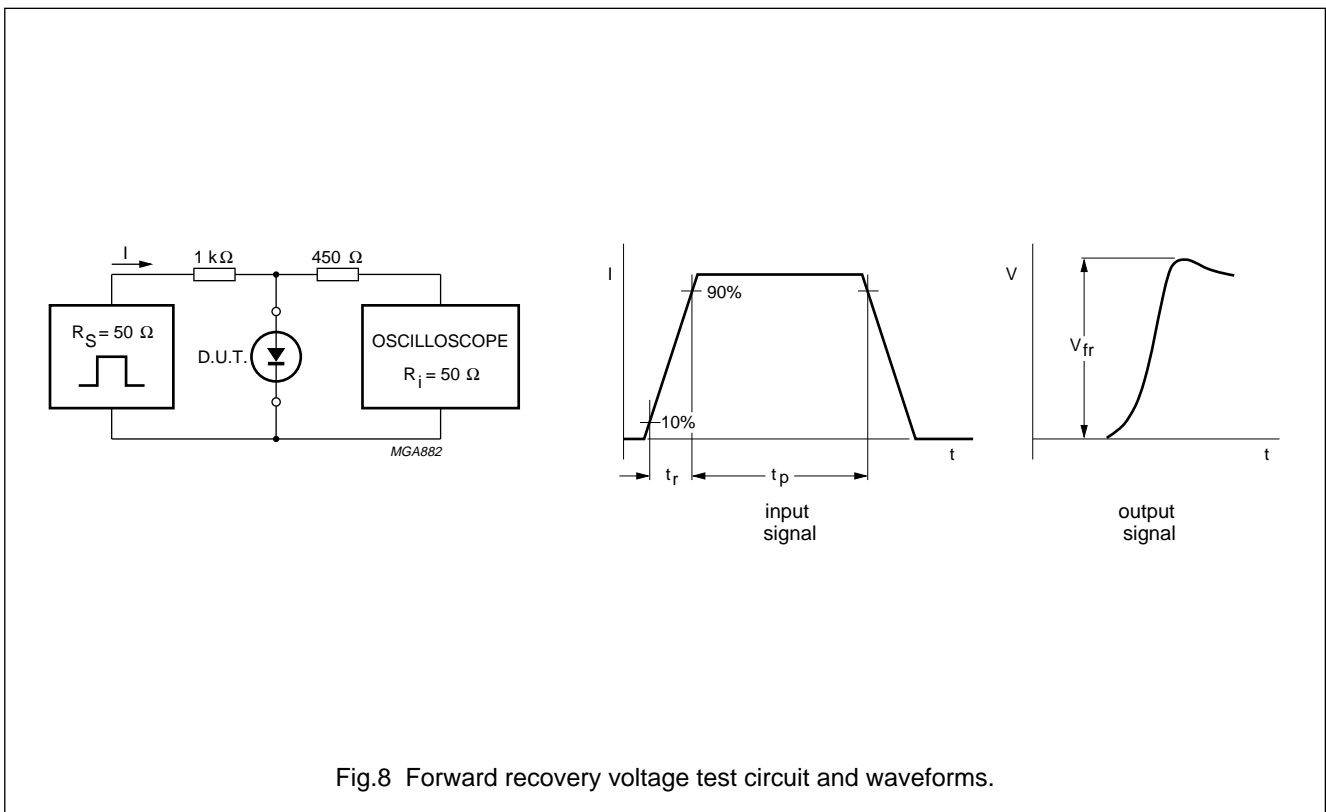


Fig.8 Forward recovery voltage test circuit and waveforms.





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